

Jerzy Kanicki

1980 – 2015: Publications

- 1978 – 1982: *Universite Libre de Bruxelles, Bruxelles, Belgium*
- 1983 – 1994: *IBM Thomas J Watson Research Center, Yorktown Heights, NY*
- 1994 – present: *College of Engineering (EECS Department), University of Michigan, Ann Arbor, MI*

Contents:

- ✓ Books
- ✓ Book Chapters
- ✓ Conference Proceedings – editor
- ✓ Journal Special Issues – editor
- ✓ Refereed Journal Publications
- ✓ Conference Proceedings
- ✓ Seminar and Workshop Lecture Notes

BOOKS

1. “*Amorphous & Microcrystalline Semiconductor Devices: Optoelectronic Devices*,” Jerzy Kanicki, Artech House, Inc., Boston, MA, 1991.
2. “*Amorphous & Microcrystalline Semiconductor Devices: Materials and Device Physics*,” Jerzy Kanicki, Artech House, Inc., Boston, MA, 1992.
3. “*High-Fidelity Medical Imaging Displays*,” A. Badano, M.J. Flynn and J. Kanicki, SPIE Press: Bellingham, WA, 2004 (ISBN 0-8194-5191-6).

BOOK CHAPTERS

1. “*Polymeric Semiconductor Contacts and Photovoltaic Application*,” J. Kanicki, in **Handbook of Conducting Polymers**, ed. T.A. Skotheim (Marcel Dekker, New York), pp. 543-660 (1986).
2. “*Properties of Metal/Hydrogenated Amorphous Silicon Interfaces*,” J. Kanicki, in **Amorphous & Microcrystalline Devices, vol. II: Materials and Device Physics**, ed. J. Kanicki (Artech House, Boston), pp. 189-282 (1992).
3. “*Optically Induced Nitrogen Dangling Bonds in Amorphous Hydrogenated Silicon Nitride Thin Film*,” W.L. Warren, J. Kanicki, P.J. McWhorter and E.H. Poindexter, in the **Physics and Chemistry of SiO₂ Interface**, eds. C.R. Helms and B.E. Deal (Plenum Press, NY, 1993).
4. “*Hydrogenated Amorphous Silicon Thin-Film Transistors*,” J. Kanicki and S. Martin, in **Thin-Film Transistors**, eds. C.R. Kagan and P. Andry (Marcel Dekker, Inc., New York), pp.71-137 (2003).
5. “*Organic Polymer Field-Effect Transistors*,” J. Kanicki and S. Martin, in **Printed Organic and Molecular Electronics**, eds.: D.R. Gamota, P. Brazis, K. Kalyanasundaram and J. Zhang (Kluwer Academic Publishers, Boston, MA), pp. 423-492 (2004).

CONFERENCE PROCEEDINGS – EDITOR

1. “*Amorphous Insulating Thin Films*,” eds. J. Kanicki, W.L. Warren, R.A.D. Devine and M. Matsumura, **Materials Research Society Symposium Proceedings**, vol. 284, 1-636, 1993.
2. “*Flat Panel Display Materials II*,” eds. M.K. Hatalis, J. Kanicki, Ch.J. Summers and F. Funda, **Materials Research Society Symposium Proceedings**, vol. 424, pp. 1-513, 1997.
3. “*Amorphous and Crystalline Insulating Thin Films - 1996*,” eds. W.L. Warren, R.A.B. Devine, M. Matsumura, S. Cristoloveanu, Y. Homma and J. Kanicki, **Materials Research Society Symposium Proceedings**, vol. 446, pp. 1-450, 1997.
4. “*Amorphous Insulating Thin Films II*,” eds. R.A.B. Devine, W.L. Warren, J. Kanicki and M. Matsumura, **European Materials Research Society Symposia Proceedings**, vol. 46, pp. 1-510, 1995.

JOURNAL SPECIAL ISSUES - EDITOR

1. “*Amorphous Semiconductor Devices*,” ed. Jerzy Kanicki, **IEEE Transactions on Electron Devices**, Special Issue, December 1989.
2. “*Amorphous Insulating Thin Films II*,” eds. R.A.B. Devine, W.L. Warren, J. Kanicki and M. Matsumura, **Journal of Non-Crystalline Solids**, Special Issue, vol. 1987, pp. 1-510, 1995.

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2. "Junction Formation Between Undoped Polyacetylene and Metals," E. Vander Donckt and J. Kanicki, **Europ. Pol. J.**, vol. 16, pp. 677-678 (1980).
3. "Electrical Conductivity and Infrared Absorption of trans-Polyacetylene in the Presence of Iodine," J. Kanicki, E. Vander Donckt and S. Boue, **J. Chem. Soc., Fard. Trans. 2**, vol. 77, pp. 2157-2168 (1981).
4. "Photovoltaic Properties of Poly-2-Vinylpyridine Iodine Complex-SnO₂ System," E. Vader Donckt, B. Noirhomme and J. Kanicki, **J. Appl. Polym. Sci.**, vol. 27, pp. 1-9 (1982).
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6. "Novel Approach to the Study of Electrical Conduction in Bromine-Doped Polyacetylene," J. Kanicki, S. Boue and E. Vander Donckt, **Thin Solid Films**, vol. 92, pp. 243-251 (1982).
7. "Photovoltaic Devices Involving Organic Polymers," J. Kanicki, **Polymer Preprints**, vol. 23, pp. 138-139 (1982).
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9. "Review of Conductor - Polymeric Semiconductor Solar Cells," J. Kanicki, **J. Phys. (Paris)**, vol. 44 C3, pp. 529-535 (1983).
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